

MOSFET - Power, Single N-Channel, SUPERFET® V, FAST, Power88

600 V, 185 mΩ, 15 A

NTMT185N60S5H

Description

The SUPERFET V MOSFET FAST series helps maximize system efficiency by the extremely low switching losses in hard switching application. The Power88 package which is an ultra-slim SMD package offers excellent switching performance by providing kelvin source configuration and lower parasitic source inductance.

Features

- 650 V @ $T_J = 150^\circ\text{C}$ / Typ. $R_{DS(on)} = 148\text{ m}\Omega$
- 100% Avalanche Tested / MSL1 Qualified
- Kelvin Source Configuration and Low Parasitic Source Inductance
- Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Computing / Display Power Supplies
- Telecom / Server Power Supplies
- Lighting / Charger/ Adapter / Industrial Power Supplies

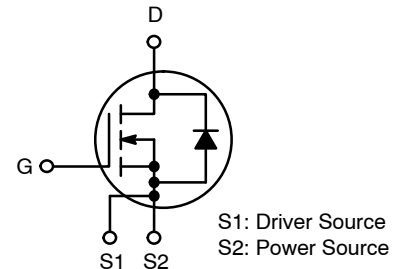
ABSOLUTE MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$, Unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	600	V
Gate-to-Source Voltage	DC	V_{GSS}	± 30
		AC ($f > 1\text{ Hz}$)	± 30
Continuous Drain Current	$T_C = 25^\circ\text{C}$	I_D	15
		$T_C = 100^\circ\text{C}$	9
Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	116
Pulsed Drain Current (Note 1)	$T_C = 25^\circ\text{C}$	I_{DM}	53
Pulsed Source Current (Body Diode) (Note 1)	$T_C = 25^\circ\text{C}$	I_{SM}	53
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$
Source Current (Body Diode)	I_S	15	A
Single Pulse Avalanche Energy	$I_L = 3.6\text{ A}, R_G = 25\text{ }\Omega$	E_{AS}	124
Avalanche Current	I_{AS}	3.6	A
Repetitive Avalanche Energy (Note 1)	E_{AR}	1.16	mJ
MOSFET dv/dt	dv/dt	120	V/ns
Peak Diode Recovery dv/dt (Note 2)		20	
Lead Temperature for Soldering Purposes (1/8" from case for 10 seconds)	T_L	260	$^\circ\text{C}$

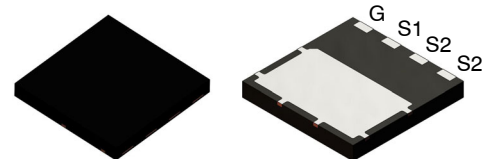
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. $I_{SD} \leq 7.5\text{ A}$, $di/dt \leq 200\text{ A}/\mu\text{s}$, $V_{DD} \leq 400\text{ V}$, starting $T_J = 25^\circ\text{C}$.

V_{DSS}	$R_{DS(ON)}\text{ MAX}$	$I_D\text{ MAX}$
600 V	185 mΩ @ 10 V	15 A

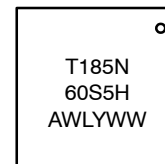


POWER MOSFET



TDFN4 8x8 2P
CASE 520AB

MARKING DIAGRAM



T185N60S5H = Specific Device Code
A = Assembly Location
WL = Wafer Lot
Y = Year
WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
NTMT185N60S5H	TDFN4	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NTMT185N60S5H

THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case, Max.	$R_{\theta JC}$	1.08	°C/W
Thermal Resistance, Junction-to-Ambient, Max.	$R_{\theta JA}$	45	

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
-----------	--------	-----------------	-----	-----	-----	------

OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}, T_J = 25^\circ\text{C}$	600	–	–	V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$\Delta V_{(BR)DSS} / \Delta T_J$	$I_D = 10\text{ mA}$, Referenced to 25°C	–	630	–	mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 600\text{ V}, T_J = 25^\circ\text{C}$	–	–	2	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 30\text{ V}, V_{DS} = 0\text{ V}$	–	–	±100	nA

ON CHARACTERISTICS

Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 7.5\text{ A}, T_J = 25^\circ\text{C}$	–	148	185	mΩ
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}, I_D = 1.4\text{ mA}, T_J = 25^\circ\text{C}$	2.7	–	4.3	V
Forward Trans-conductance	g_{FS}	$V_{DS} = 20\text{ V}, I_D = 7.5\text{ A}$	–	18	–	S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}, f = 250\text{ kHz}$	–	1350	–	pF
Output Capacitance	C_{OSS}		–	25	–	
Time Related Output Capacitance	$C_{OSS(tr)}$	$I_D = \text{Constant}, V_{DS} = 0\text{ V to } 400\text{ V}, V_{GS} = 0\text{ V}$	–	372	–	
Energy Related Output Capacitance	$C_{OSS(er)}$		–	42	–	
Total Gate Charge	$Q_{G(tot)}$	$V_{DD} = 400\text{ V}, I_D = 7.5\text{ A}, V_{GS} = 10\text{ V}$	–	25	–	nC
Gate-to-Source Charge	Q_{GS}		–	7	–	
Gate-to-Drain Charge	Q_{GD}		–	8	–	
Gate Resistance	R_G	$f = 1\text{ MHz}$	–	0.9	–	Ω

SWITCHING CHARACTERISTICS

Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 0/10\text{ V}, V_{DD} = 400\text{ V}, I_D = 7.5\text{ A}, R_G = 10\text{ }\Omega$	–	18	–	ns
Rise Time	t_r		–	8	–	
Turn-Off Delay Time	$t_{d(off)}$		–	52	–	
Fall Time	t_f		–	4.3	–	

SOURCE-TO-DRAIN DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_{SD} = 7.5\text{ A}, T_J = 25^\circ\text{C}$	–	–	1.2	V
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, I_{SD} = 7.5\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, V_{DD} = 400\text{ V}$	–	213	–	ns
Reverse Recovery Charge	Q_{RR}		–	2368	–	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

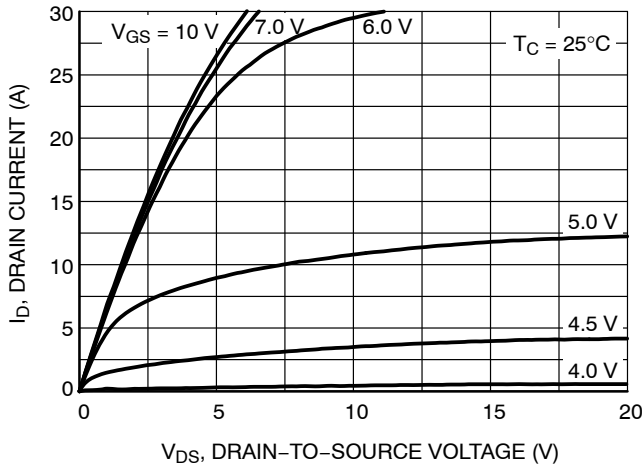


Figure 1. On-Region Characteristics

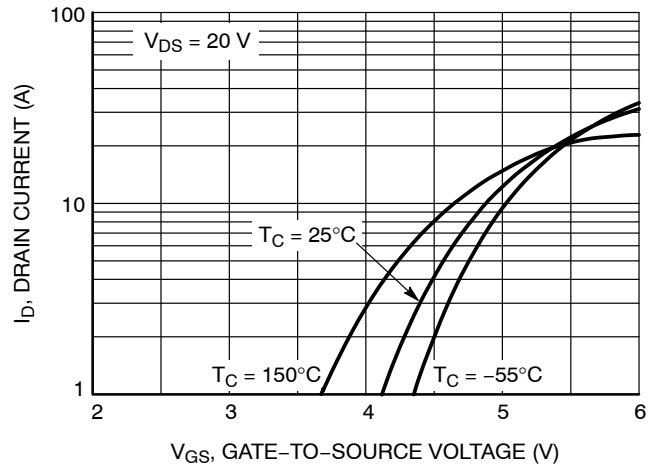


Figure 2. Transfer Characteristics

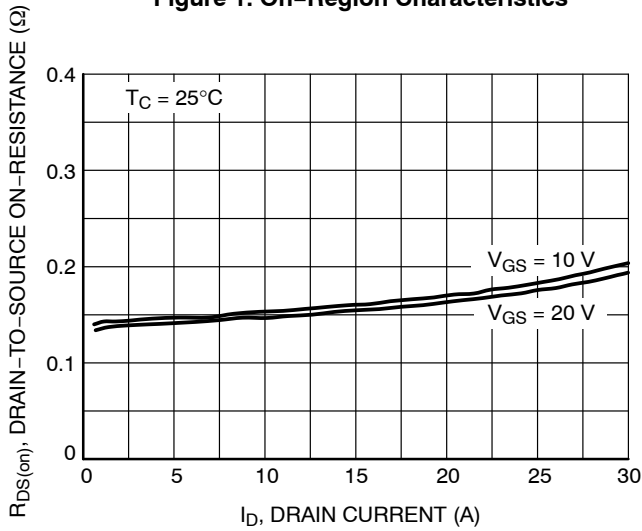


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

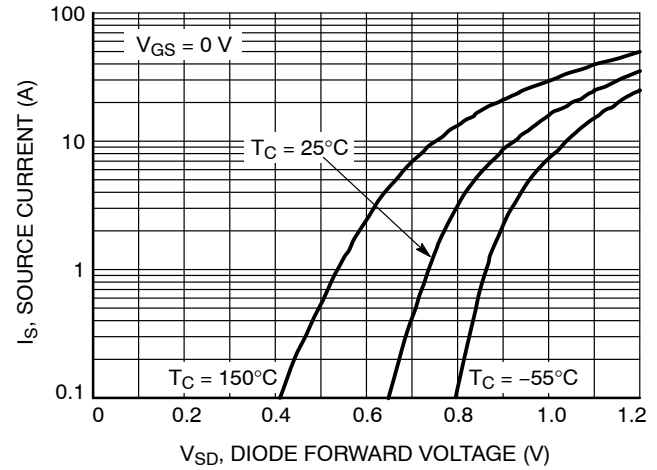


Figure 4. Diode Forward Voltage vs. Source Current

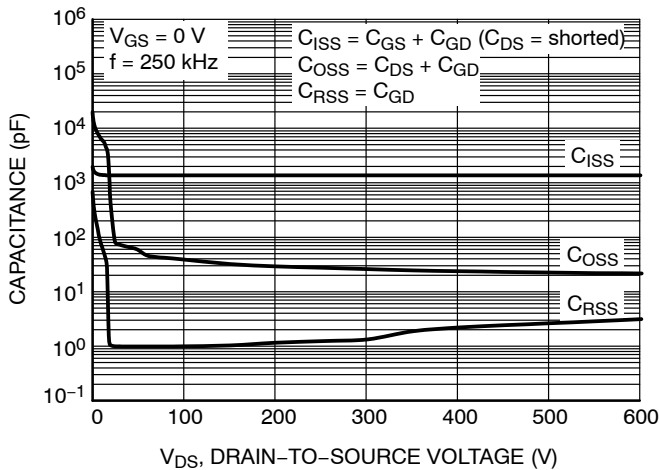


Figure 5. Capacitance Characteristics

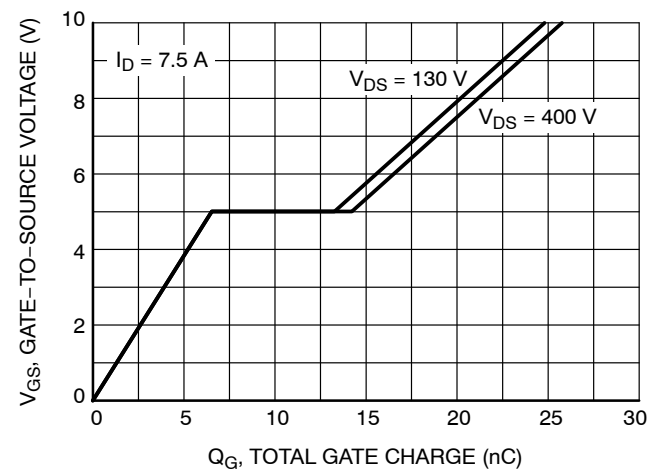


Figure 6. Gate Charge Characteristics

TYPICAL CHARACTERISTICS

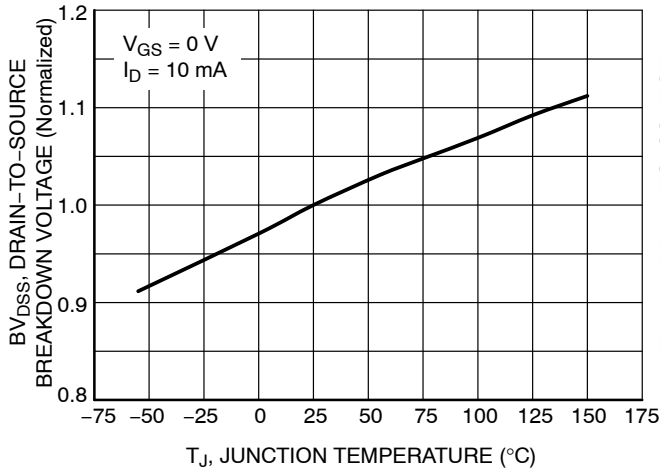


Figure 7. Breakdown Voltage Variation vs. Temperature

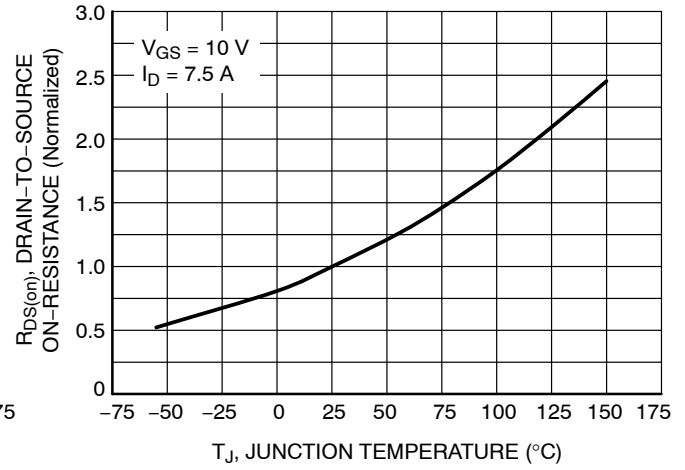


Figure 8. On-Resistance Variation vs. Temperature

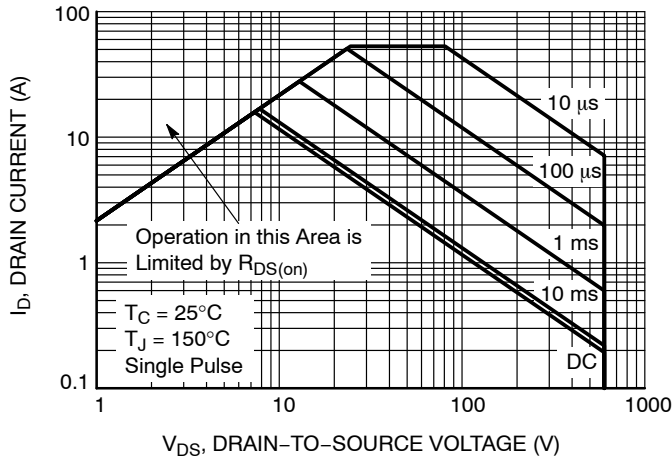


Figure 9. Maximum Safe Operating Area

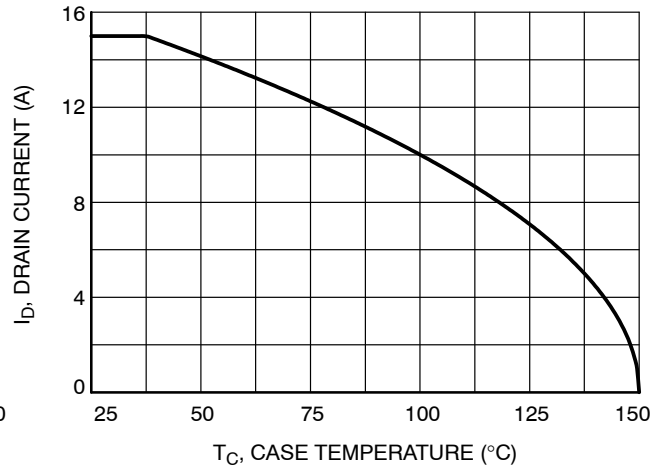


Figure 10. Maximum Drain Current vs. Case Temperature

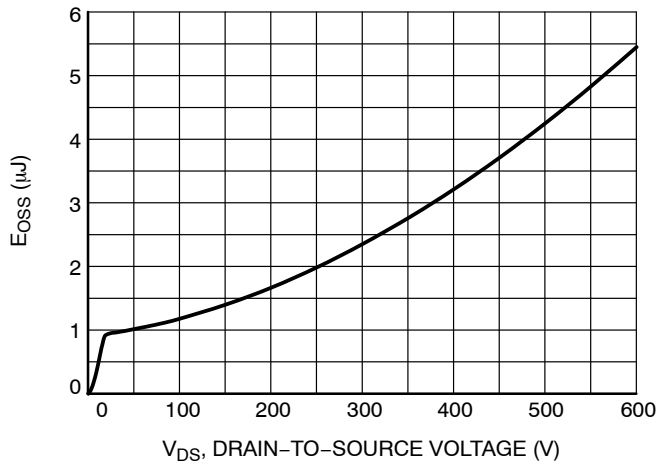


Figure 11. E_{OSS} vs. Drain-to-Source Voltage

NTMT185N60S5H

TYPICAL CHARACTERISTICS

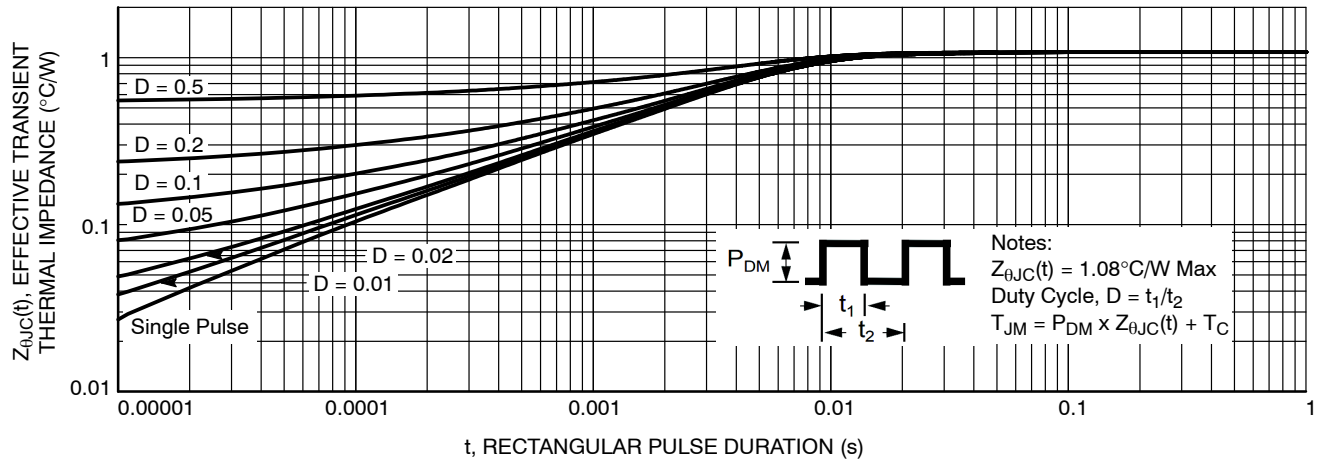


Figure 12. Transient Thermal Impedance

NTMT185N60S5H

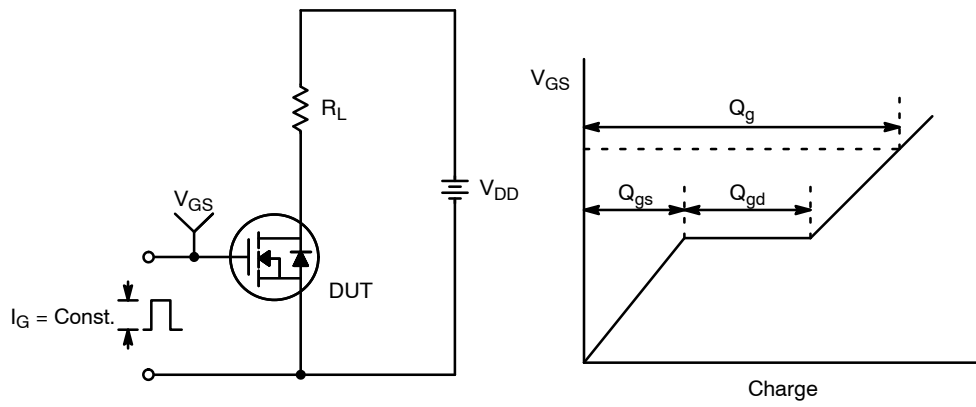


Figure 13. Gate Charge Test Circuit & Waveform

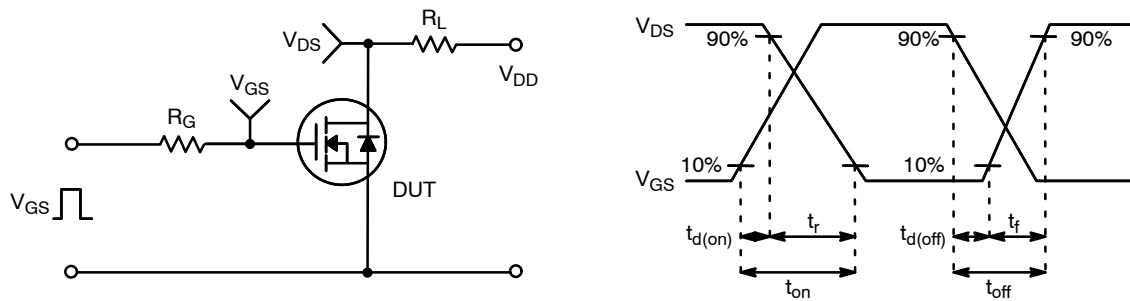


Figure 14. Resistive Switching Test Circuit & Waveforms

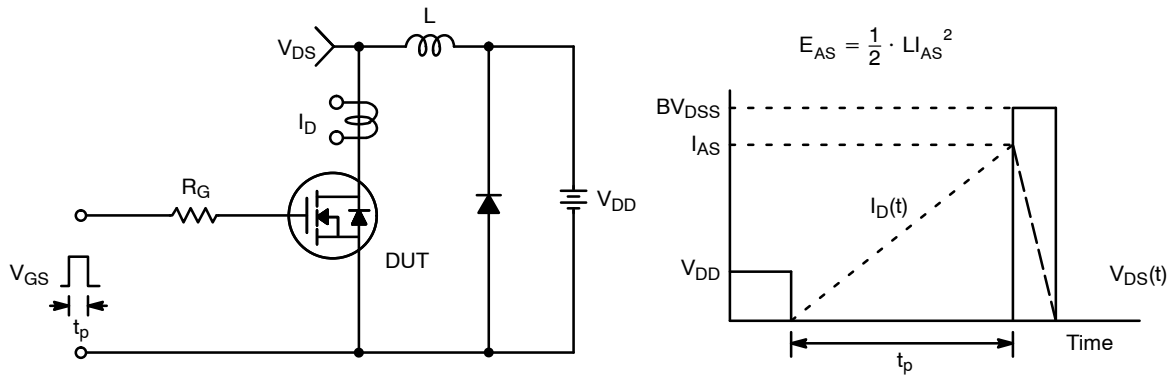


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

NTMT185N60S5H

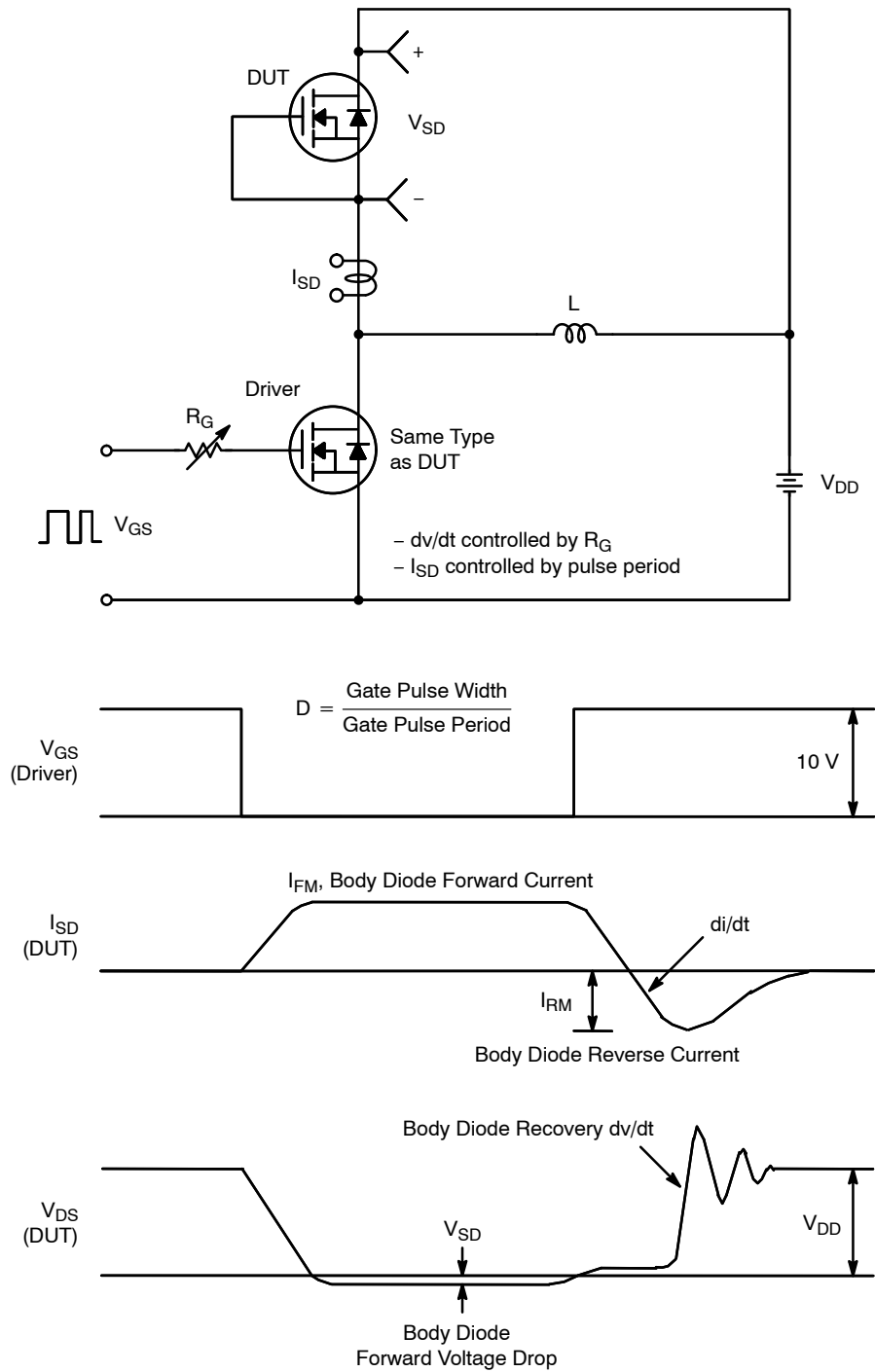


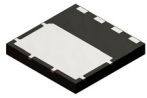
Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®

ON

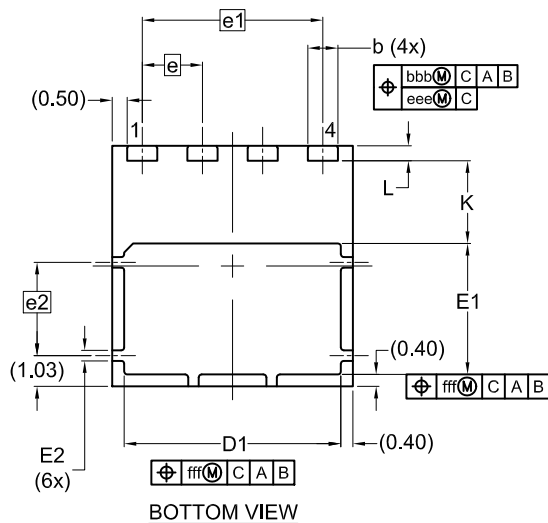
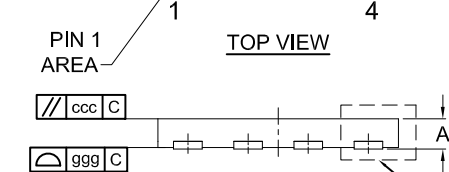
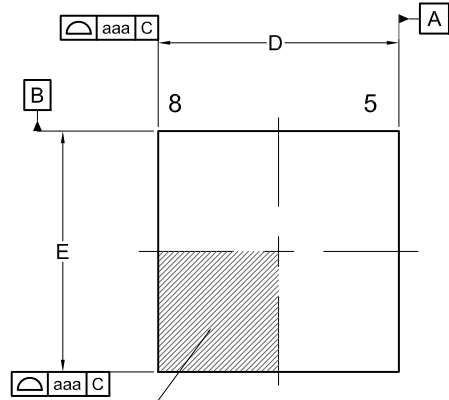


TDFN4 8x8, 2P

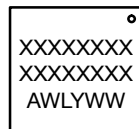
CASE 520AB

ISSUE O

DATE 24 APR 2019

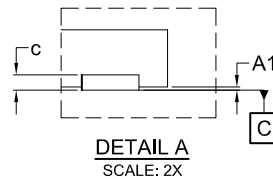


GENERIC MARKING DIAGRAM*

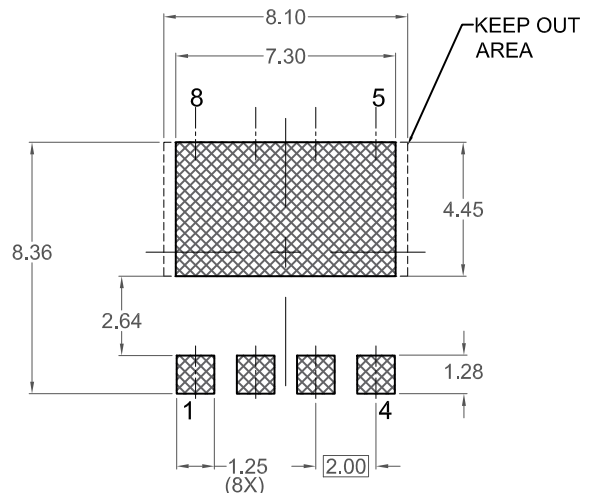


XXXX = Specific Device Code
 A = Assembly Location
 L = Wafer Lot
 Y = Year
 W = Work Week
 ■ = Pb-Free Package

NOTES: UNLESS OTHERWISE SPECIFIED
 A) DOES NOT FULLY CONFORM TO JEDEC REGISTRATION MO-220.
 B) ALL DIMENSIONS ARE IN MILLIMETERS.
 C) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
 D) IT IS RECOMMENDED TO HAVE NO TRACES OR VIAS WITHIN THE KEEP OUT AREA.



DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0.00	--	0.05
b	0.90	1.00	1.10
c	0.10	0.20	0.30
D	7.90	8.00	8.10
D1	7.10	7.20	7.30
E	7.90	8.00	8.10
E1	4.25	4.35	4.45
E2	0.15	0.25	0.35
e	2.00 BSC		
e1	6.00 BSC		
e2	3.10 BSC		
K	(2.75)		
L	0.40	0.50	0.60
aaa	0.10		
bbb	0.10		
ccc	0.05		
eee	0.05		
fff	0.10		
ggg	0.15		



RECOMMENDED LAND PATTERN

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	98AON73688G	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	TDFN4 8x8, 2P	PAGE 1 OF 1

ON Semiconductor and ON are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT

North American Technical Support:

Voice Mail: 1 800-282-9855 Toll Free USA/Canada

Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative